

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Patent No.7,018,908
Patent Issue Date March 28, 2006
Application Serial No. 10/815,065
Filing Date March 30, 2004
Assignee Micron Technology, Inc.
Inventorship Sujit Sharan
Attorney's Docket No.MI22-1421
Title: Methods of Forming Silicon Dioxide Layers, And Methods of Forming
Trench Isolation Regions

REQUEST FOR CERTIFICATE OF CORRECTION OF PATENT
FOR PTO MISTAKE (37 C.F.R. 1.322(a))

To: Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450
ATTN: Decision and Certificate of Correction
Branch of the Patent Issue Division

From: James E. Lake (Tel. 509-624-4276; Fax 509-838-3424)
Wells St. John P.S.
601 W. First Avenue, Suite 1300
Spokane, WA 99201-3828

Sir:

It is hereby requested that a Certificate of Correction be issued with respect to Patent No. 7,018,908, granted March 28, 2006, in accordance with the Certificate of Correction form attached hereto in duplicate.

The errors listed on the Certificate of Correction form were apparently incurred through the fault of the PTO as will be disclosed by the records of files in the Office.

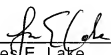
Since this Certificate of Correction is being requested due to PTO errors, it is believed that no fee is due. However, in the event that a fee is required for issuance of this Certificate of Correction, please charge the fee specified under

37 C.F.R. § 1.20(a) to Deposit Account No. 23-0925. Please credit Deposit Account No. 23-0925 with any overpayment of the above fee.

Attached hereto, in duplicate is Form PTO-1050, with at least one copy being suitable for printing.

Respectfully submitted,

Dated: 22 Aug 2007

By: 
James E. Lake
Reg. No. 44,854

UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION

PATENT NO. : 7,018,908 B2

APPLICATION NO.: 10/815,065

ISSUE DATE : March 28, 2006

INVENTOR(S) : Sujit Sharan

It is certified that an error or errors appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Col. 5, line 27 –

Replace “silicon dioxide layer is comprised by a shallow trench”
Insert --silicon dioxide layer is comprised by a shallow trench--

Col. 5, line 56 –

Replace “forming era opening extending into a substrate;”
Insert --forming an opening extending into a substrate;--

Col. 6, line 35 –

Replace “contacts the fleet layer”
Insert --contacts the first layer—

Col. 7, line 4 –

Replace “layers within the opening end the forming of the second”
Insert --layers within the opening and the forming of the second--

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